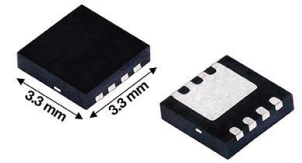




New SiSS94DN 200 V N-Channel MOSFET in 10.89 mm² PowerPAK[®] 1212-8S Package Offers Industry-Low Typical R_{DS(ON)} of 61 mΩ and FOM of 854 mΩ*nC to Increase Power Density, Save Energy

Product Benefits:

- Reduced conduction and switching losses to save energy
 - Industry-low typical on-resistance of 61 mΩ at 10 V
 - Typical Q_g of 14 nC
 - Improved on-resistance times gate charge — a critical figure of merit (FOM) for MOSFETs used in switching applications — of 854 mΩ*nC
- Offered in the 3.3 mm by 3.3 mm thermally enhanced PowerPAK 1212-8S package
 - Compact form factor is easier to fit into designs with limited PCB real estate
- 100 % R_G- and UIS-tested
- RoHS-compliant, and halogen-free



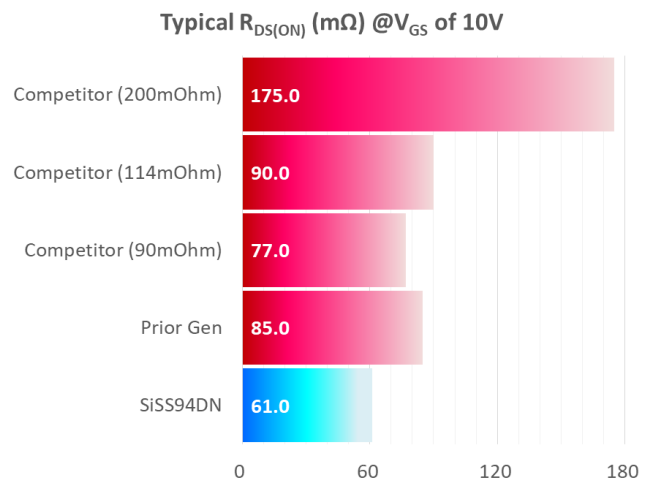
Market Applications:

- Primary-side switching for isolated DC/DC topologies and synchronous rectification in power supplies, telecom equipment, networking equipment, and consumer electronics; LED backlighting for computers, LED TVs; and motor drive control, load switching, and power conversion for GPS, factory automation, and industrial applications

The News:

Vishay Intertechnology introduces a new 200 V n-channel TrenchFET[®] Gen IV power MOSFET that offers industry-low typical on-resistance of 61 mΩ at 10 V in the 3.3 mm by 3.3 mm thermally enhanced PowerPAK 1212-8S package, in addition to improved on-resistance times gate charge of 854 mΩ*nC.

- Purpose-built to increase power density, the space-saving SiSS94DN is 65 % smaller than devices with similar on-resistance in 6 mm by 5 mm packages
- 20 % lower typical on-resistance than the next best product on the market in a similar package size
- 17 % lower FOM than the previous-generation solution
- With its compact size, the SiSS94DN allows designers to save PCB space by replacing a much larger MOSFET with the same conduction losses, or a similar sized MOSFET with higher conduction losses





The Key Specifications:

- Package: PowerPAK 1212-8S
- Drain-source voltage: 200 V
- Maximum on-resistance:
 - At 10 V: 75 m Ω
 - At 7.5 V: 78 m Ω
- Typical on-resistance:
 - At 10 V: 61 m Ω
 - At 7.5 V: 63 m Ω
- Typical gate charge:
 - At 10 V: 14 nC
 - At 7.5 V: 11 nC

Availability:

Samples and production quantities of the SiSS94DN are available now, with lead times of 12 weeks.

To access the product datasheet on the Vishay Website, go to <http://www.vishay.com/ppg?77350> (SiSS94DN)

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